National Semiconductor

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LM3046
Transistor Array

General Description

The LM3046 consists of five general purpose silicon NPN transistors on a common monolithic substrate. Two of the transistors are internally connected to form a differentially-connected pair. The transistors are well suited to a wide variety of applications in low power system in the DC through VHF range. They may be used as discrete transistors in conventional circuits however, in addition, they provide the very significant inherent integrated circuit advantages of close electrical and thermal matching. The LM3046 is supplied in a 14-lead molded small outline package.

Features

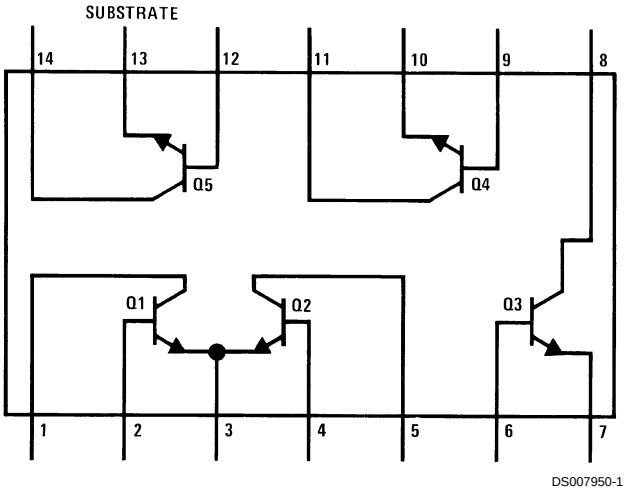
- Two matched pairs of transistors
  V_{BE} matched ±5 mV
  Input offset current 2 µA max at I_C = 1 mA
- Five general purpose monolithic transistors
- Operation from DC to 120 MHz
- Wide operating current range
- Low noise figure: 3.2 dB typ at 1 kHz

Applications

- General use in all types of signal processing systems operating anywhere in the frequency range from DC to VHF
- Custom designed differential amplifiers
- Temperature compensated amplifiers

Schematic and Connection Diagram

Small Outline Package



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Top View
Order Number LM3046M
See NS Package Number M14A

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications. (T_A = 25˚C)

	LM3046		
	Each Transistor	**Total Package**	**Units**
Power Dissipation:			
T_A = 25˚C	300	750	mW
T_A = 25˚C to 55˚C	300	750	mW
T_A > 55˚C	Derate at 6.67		mW/˚C
T_A = 25˚C to 75˚C			mW
T_A > 75˚C			mW/˚C
Collector to Emitter Voltage, V_{CEO}	15		V
Collector to Base Voltage, V_{CBO}	20		V
Collector to Substrate Voltage, V_{CIO} (Note 2)	20		V
Emitter to Base Voltage, V_{EBO}	5		V
Collector Current, I_C	50		mA
Operating Temperature Range	−40˚C to +85˚C		
Storage Temperature Range	−65˚C to +85˚C		
Soldering Information			
Dual-In-Line Package Soldering (10 Sec.)	260˚C		
Small Outline Package			
Vapor Phase (60 Seconds)	215˚C		
Infrared (15 Seconds)	220˚C		

See AN-450 “Surface Mounting Methods and Their Effect on Product Reliability” for other methods of soldering surface mount devices.

Electrical Characteristics

(T_A = 25˚C unless otherwise specified)

Parameter	Conditions	Limits			Units
		Min	**Typ**	**Max**	
Collector to Base Breakdown Voltage ($V_{(BR)CBO}$)	I_C = 10 µA, I_E = 0	20	60		V
Collector to Emitter Breakdown Voltage ($V_{(BR)CEO}$)	I_C = 1 mA, I_B = 0	15	24		V
Collector to Substrate Breakdown Voltage ($V_{(BR)CIO}$)	I_C = 10 µA, I_{CI} = 0	20	60		V
Emitter to Base Breakdown Voltage ($V_{(BR)EBO}$)	I_E 10 µA, I_C = 0	5	7		V
Collector Cutoff Current (I_{CBO})	V_{CB} = 10V, I_E = 0		0.002	40	nA
Collector Cutoff Current (I_{CEO})	V_{CE} = 10V, I_B = 0			0.5	µA
Static Forward Current Transfer Ratio (Static Beta) (h_{FE})	V_{CE} = 3V, I_C = 10 mA		100		
	I_C = 1 mA	40	100		
	I_C = 10 µA		54		
Input Offset Current for Matched Pair Q_1 and Q_2 $\lvert I_{O1} - I_{IO2}\rvert$	V_{CE} = 3V, I_C = 1 mA		0.3	2	µA
Base to Emitter Voltage (V_{BE})	V_{CE} = 3V, I_E = 1 mA		0.715		V
	I_E = 10 mA		0.800		
Magnitude of Input Offset Voltage for Differential Pair $\lvert V_{BE1} - V_{BE2}\rvert$	V_{CE} = 3V, I_C = 1 mA		0.45	5	mV
Magnitude of Input Offset Voltage for Isolated Transistors $\lvert V_{BE3} - V_{BE4}\rvert$, $\lvert V_{BE4} - V_{BE5}\rvert$, $\lvert V_{BE5} - V_{BE3}\rvert$	V_{CE} = 3V, I_C = 1 mA		0.45	5	mV
Temperature Coefficient of Base to Emitter Voltage $\left(\frac{\Delta V_{BE}}{\Delta T}\right)$	V_{CE} = 3V, I_C = 1 mA		−1.9		mV/˚C
Collector to Emitter Saturation Voltage ($V_{CE(SAT)}$)	I_B = 1 mA, I_C = 10 mA		0.23		V

Electrical Characteristics (Continued)

(T_A = 25˚C unless otherwise specified)

Parameter	Conditions	Limits			Units
		Min	Typ	Max	
Temperature Coefficient of Input Offset Voltage $\left(\frac{\Delta V_{10}}{\Delta T}\right)$	V_{CE} = 3V, I_C = 1 mA		1.1		µV/˚C

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.

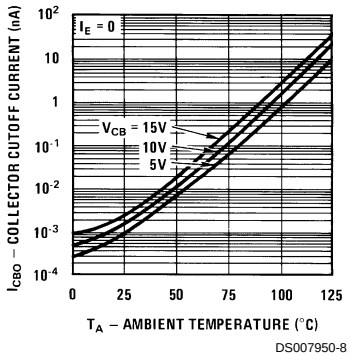
Note 2: The collector of each transistor is isolated from the substrate by an integral diode. The substrate (terminal 13) must be connected to the most negative point in the external circuit to maintain isolation between transistors and to provide for normal transistor action.

Electrical Characteristics

Parameter	Conditions	Min	Typ	Max	Units
Low Frequency Noise Figure (NF)	f = 1 kHz, V_{CE} = 3V, I_C = 100 µA, R_S = 1 kΩ		3.25		dB
LOW FREQUENCY, SMALL SIGNAL EQUIVALENT CIRCUIT CHARACTERISTICS					
Forward Current Transfer Ratio (h_{fe})	f = 1 kHz, V_{CE} = 3V, I_C = 1 mA		110		
Short Circuit Input Impednace (h_{ie})			3.5		kΩ
Open Circuit Output Impedance (h_{oe})			15.6		µmho
Open Circuit Reverse Voltage Transfer Ratio (h_{re})			1.8×10^{-4}		
ADMITTANCE CHARACTERISTICS					
Forward Transfer Admittance (Y_{fe})	f = 1 MHz, V_{CE} = 3V, I_C = 1 mA		31 − j 1.5		
Input Admittance (Y_{ie})			0.3+J 0.04		
Output Admittance (Y_{oe})			0.001+j 0.03		
Reverse Transfer Admittance (Y_{re})			See Curve		
Gain Bandwidth Product (f_T)	V_{CE} = 3V, I_C = 3 mA	300	550		
Emitter to Base Capacitance (C_{EB})	V_{EB} = 3V, I_E = 0		0.6		pF
Collector to Base Capacitance (C_{CB})	V_{CB} = 3V, I_C = 0		0.58		pF
Collector to Substrate Capacitance (C_{CI})	V_{CS} = 3V, I_C = 0		2.8		pF

Typical Performance Characteristics

Typical Collector To Base Cutoff Current vs Ambient Temperature for Each Transistor



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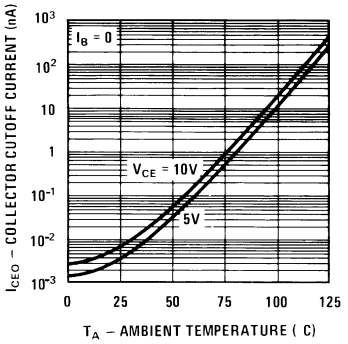
Typical Collector To Emitter Cutoff Current vs Ambient Temperature for Each Transistor



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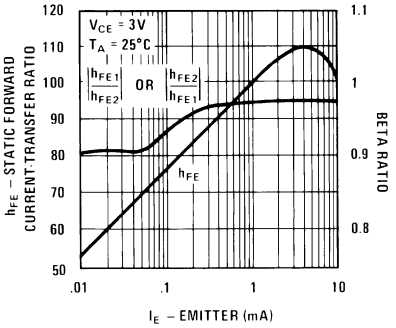
Typical Static Forward Current-Transfer Ratio and Beta Ratio for Transistors Q_1 and Q_2 vs Emitter Current



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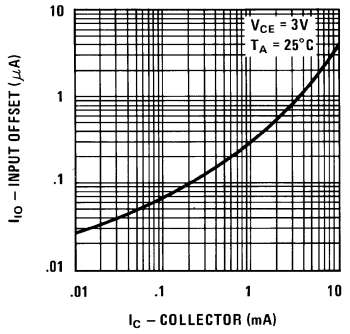
Typical Performance Characteristics (Continued)

Typical Input Offset Current for Matched Transistor Pair Q_1 Q_2 vs Collector Current



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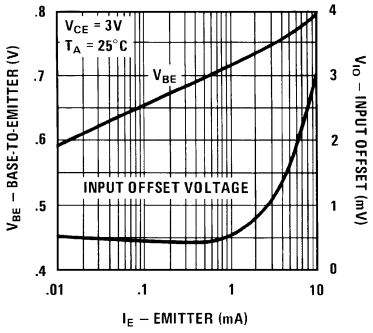
Typical Static Base To Emitter Voltage Characteristic and Input Offset Voltage for Differential Pair and Paired Isolated Transistors vs Emitter Current



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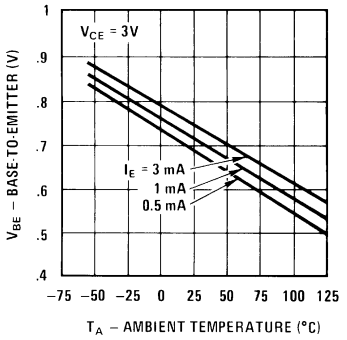
Typical Base To Emitter Voltage Characteristic for Each Transistor vs Ambient Temperature



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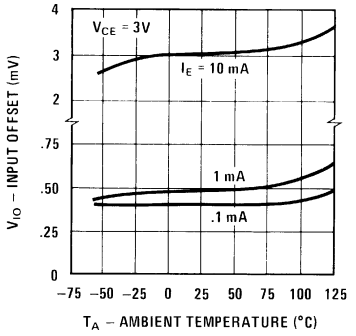
Typical Input Offset Voltage Characteristics for Differential Pair and Paired Isolated Transistors vs Ambient Temperature



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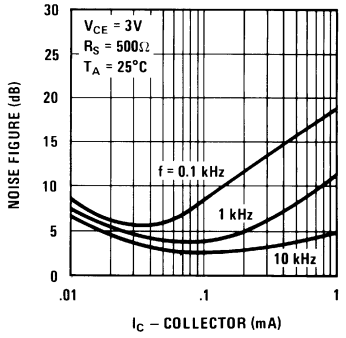
Typical Noise Figure vs Collector Current



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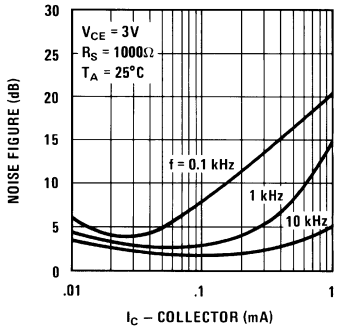
Typical Noise Figure vs Collector Current



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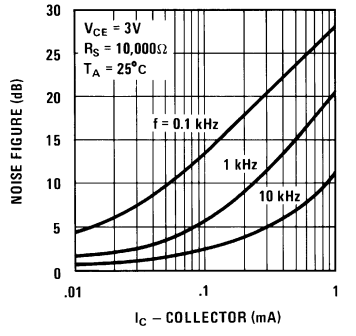
Typical Noise Figure vs Collector Current



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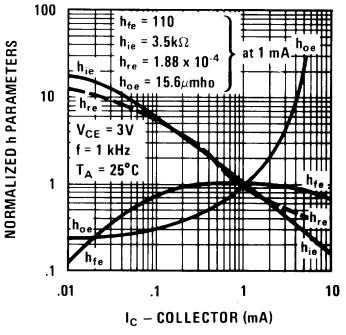
Typical Normalized Forward Current Transfer Ratio, Short Circuit Input Impedance, Open Circuit Output Impedance, and Open Circuit Reverse Voltage Transfer Ratio vs Collector Current



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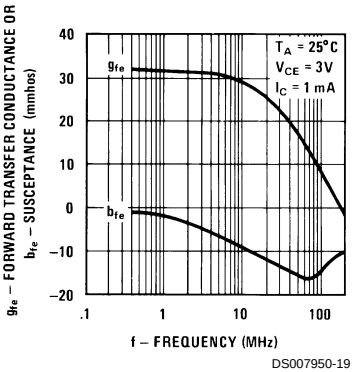
Typical Forward Transfer Admittance vs Frequency



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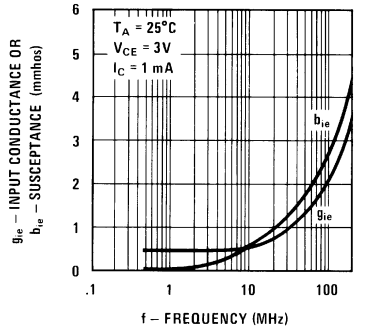
Typical Performance Characteristics (Continued)

Typical Input Admittance vs Frequency



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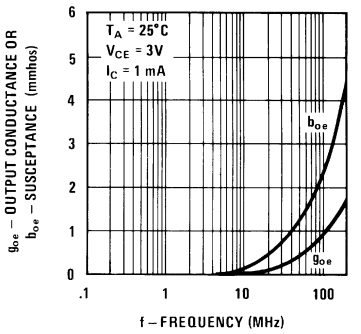
Typical Output Admittance vs Frequency



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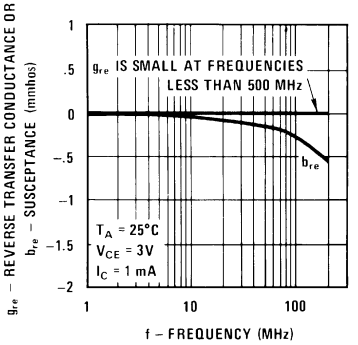
Typical Reverse Transfer Admittance vs Frequency



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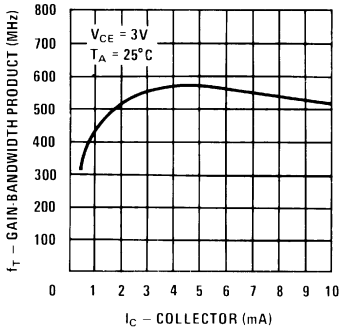
Typical Gain-Bandwidth Product vs Collector Current



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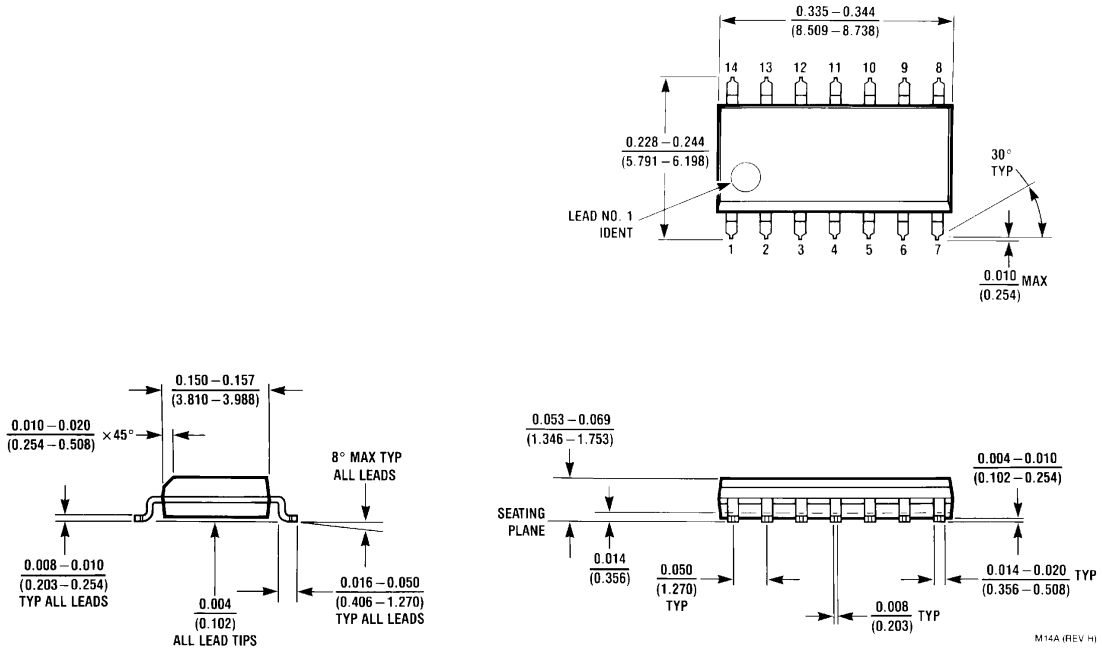
Physical Dimensions inches (millimeters) unless otherwise noted



Molded Small Outline Package (M)
Order Number LM3046M
NS Package Number M14A

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